

MA2C165, MA2C166, MA2C167

Silicon epitaxial planar type

For switching circuits

■ Features

- Short reverse recovery time t_{rr}
- Small terminal capacitance, C_t

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit	
Reverse voltage (DC)	MA2C165	V_R	35	V
	MA2C166		50	
	MA2C167		75	
Repetitive peak reverse voltage	MA2C165	V_{RRM}	35	V
	MA2C166		50	
	MA2C167		75	
Average forward current	$I_{F(AV)}$	100	mA	
Repetitive peak forward current	I_{FRM}	225	mA	
Non-repetitive peak forward surge current*	I_{FSM}	500	mA	
Junction temperature	T_j	200	$^\circ\text{C}$	
Storage temperature	T_{stg}	-55 to +200	$^\circ\text{C}$	

Note) * : $t = 1\text{ s}$

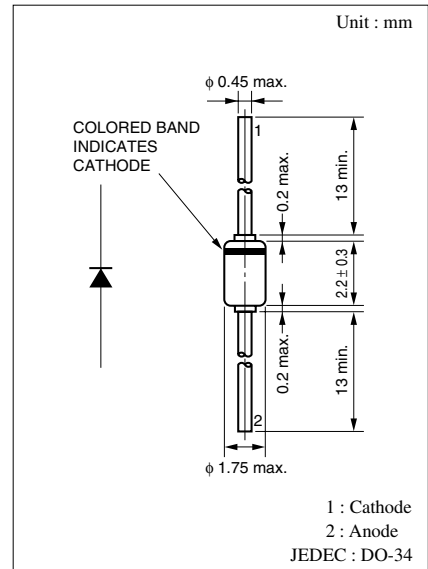
■ Electrical Characteristics $T_a = 25^\circ\text{C}$

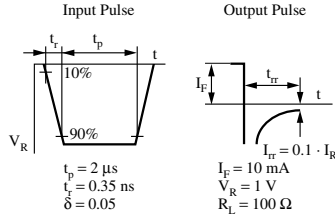
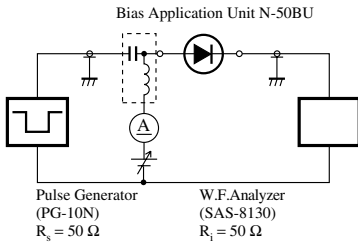
Parameter	Symbol	Conditions	Min	Typ	Max	Unit	
Reverse current (DC)	MA2C165	$V_R = 15\text{ V}$			0.025	μA	
		$V_R = 30\text{ V}$			0.1		
	MA2C166	$V_R = 15\text{ V}$			0.025		
		$V_R = 50\text{ V}$			5		
	MA2C167	$V_R = 20\text{ V}$		0.012	0.025		
		$V_R = 75\text{ V}$			5		
	MA2C165		$V_R = 35\text{ V}, T_a = 150^\circ\text{C}$				100
	MA2C166		$V_R = 50\text{ V}, T_a = 150^\circ\text{C}$				100
MA2C167		$V_R = 75\text{ V}, T_a = 150^\circ\text{C}$		50	100		
Forward voltage (DC)	V_F	$I_F = 100\text{ mA}$		0.95	1.2	V	
Reverse voltage (DC)	V_R	$I_R = 5\text{ }\mu\text{A}$	35			V	
Terminal capacitance	C_t	$V_R = 0\text{ V}, f = 1\text{ MHz}$		0.9	2	pF	
Reverse recovery time*	MA2C165	$I_F = 10\text{ mA}, V_R = 1\text{ V},$ $I_{rr} = 0.1 \cdot I_R, R_L = 100\text{ }\Omega$			10	ns	
	MA2C166/167			2.2	4		

Note) 1. Rated input/output frequency: 100 MHz (MA2C165), 250 MHz (MA2C167), 1 000 MHz (MA2C166) 2. * : t_{rr} measuring circuit

■ Cathode Indication

Type No.	MA2C165	MA2C166	MA2C167
Color	White	Green	Violet





t_{rr} measuring circuit

